

ABSTRACT OF THE DISCLOSURE

A method for reducing stress migration in the copper interconnect line is set forth. In accordance with the method, two anneal steps take place: The first step is at low temperature and of relatively short duration (e.g., about 25-300° C, and about 10 seconds-10 hours). After the first anneal, the wafer is cooled to room temperature. The second step is performed after the cooling step; a higher anneal temperature and longer time duration is needed to enhance performance.